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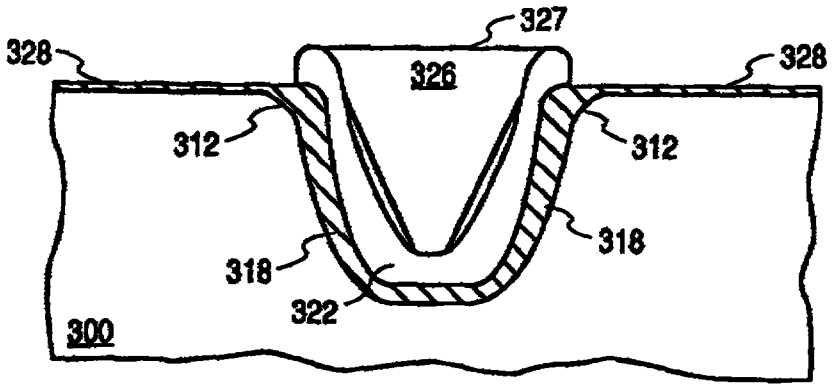
(54) Title: NOVEL SHALLOW TRENCH ISOLATION TECHNIQUE

(57) Abstract

A method of forming a trench isolation region. The method of the present invention comprises the steps of forming an opening in a semiconductor substrate, oxidizing the opening a first time, and then etching the oxidized opening with a wet etchant comprising HF. The opening is then oxidized a second time.